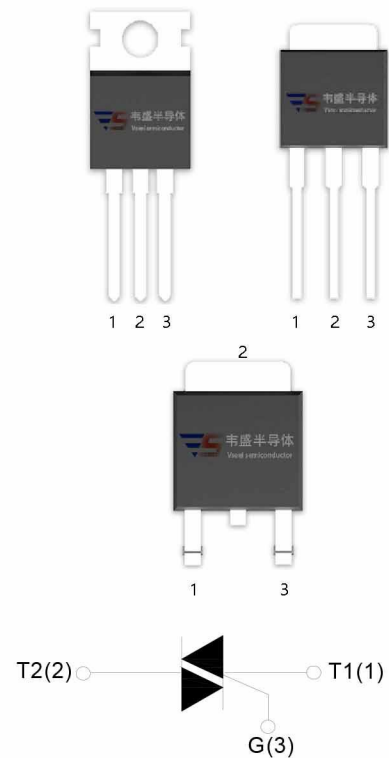


## DESCRIPTION:

**BT137-SS** triacs with low holding and latching current are especially recommended for use on middle and small resistance type power load.

## MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
$V_{DRM}/V_{RRM}$	600 and 800	V



## ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		$T_{stg}$	-40-150	°C
Operating junction temperature range		$T_j$	-40-125	°C
Repetitive peak off-state voltage( $T_j=25^{\circ}\text{C}$ )		$V_{DRM}$	600/800	V
Repetitive peak reverse voltage( $T_j=25^{\circ}\text{C}$ )		$V_{RRM}$	600/800	V
RMS on-state current	TO-251/ TO-220B(Non-Ins)/ TO-220C( $T_c=95^{\circ}\text{C}$ )	$I_{T(RMS)}$	8	A
	TO-262/ TO-220A(Ins)/ TO-220F(Ins) ( $T_c=85^{\circ}\text{C}$ )			
Non repetitive surge peak on-state current (full cycle, $F=50\text{Hz}$ )		$I_{TSM}$	65	A
$I^2t$ value for fusing ( $t_p=10\text{ms}$ )		$I^2t$	21	$\text{A}^2\text{s}$
Peak gate current		$I_{GM}$	2	A

Critical rate of rise of on-state current( $I_G=2 \times I_{GT}$ )	I - II -III	dI/dt	50	A/ $\mu$ s
	IV		10	
Average gate power dissipation		$P_{G(AV)}$	0.5	W
Peak gate power		$P_{GM}$	5	W

### ELECTRICAL CHARACTERISTICS ( $T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value				Unit
				D	E	F	G	
$I_{GT}$	$V_D=12\text{V}$ $R_L=30\Omega$	I - II -III	MAX	5	10	25	50	mA
		IV		10	25	70	100	
$V_{GT}$		ALL	MAX	1.3				V
$V_{GD}$	$V_D=V_{DRM}$ $T_J=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	ALL	MIN	0.2				V
$I_L$	$I_G=1.2I_{GT}$	I -III	MAX	10	20	50	70	mA
		II -IV		20	30	70	100	
$I_H$	$I_T=100\text{mA}$		MAX	10	15	40	60	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_J=125^\circ\text{C}$		MIN	20	50	50	200	V/ $\mu$ s

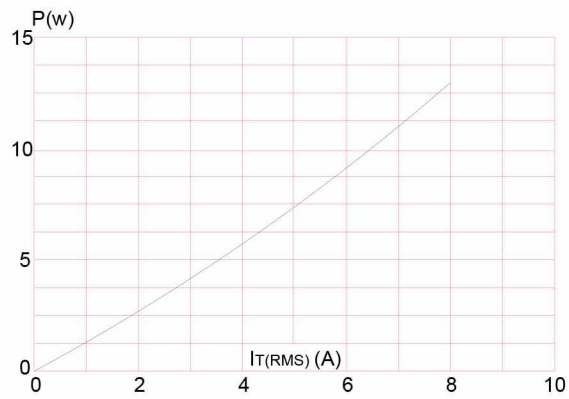
### STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
$V_{TM}$	$I_{TM}=10\text{A}$ $t_p=380\mu\text{s}$	$T_J=25^\circ\text{C}$	1.6	V
$I_{DRM}$	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_J=25^\circ\text{C}$	5	$\mu\text{A}$
$I_{RRM}$		$T_J=125^\circ\text{C}$	1	mA

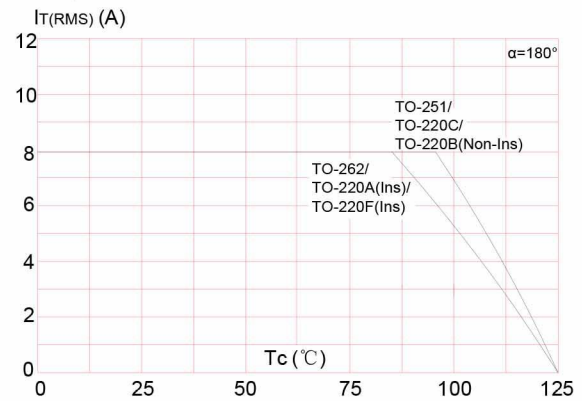
### THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-251	2.1	$^\circ\text{C}/\text{W}$
		TO-220B(Non-Ins)/ TO-220C	1.8	
		TO-220A(Ins)/ TO-220F(Ins)	2.9	
		TO-262	3.1	

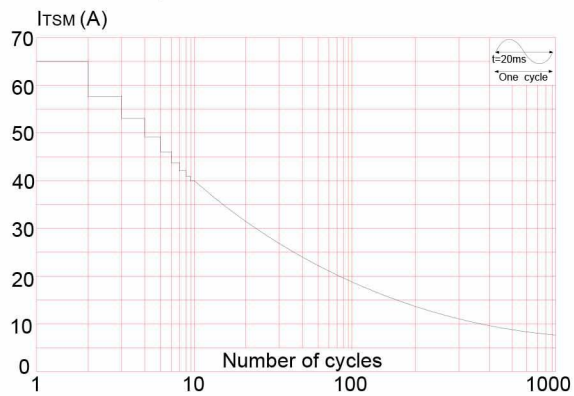
**FIG.1:** Maximum power dissipation versus RMS on-state current



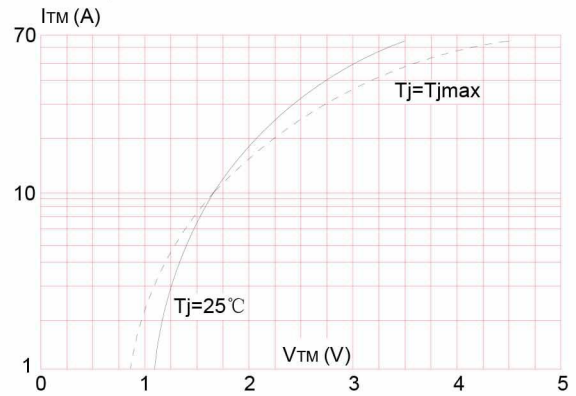
**FIG.2:** RMS on-state current versus case temperature



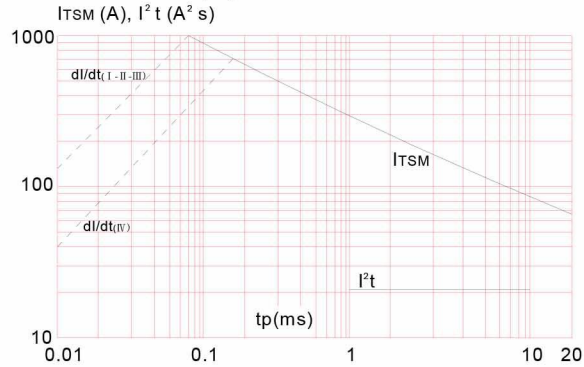
**FIG.3:** Surge peak on-state current versus number of cycles



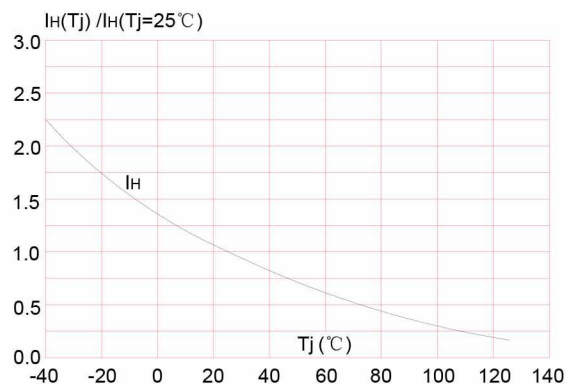
**FIG.4:** On-state characteristics (maximum values)



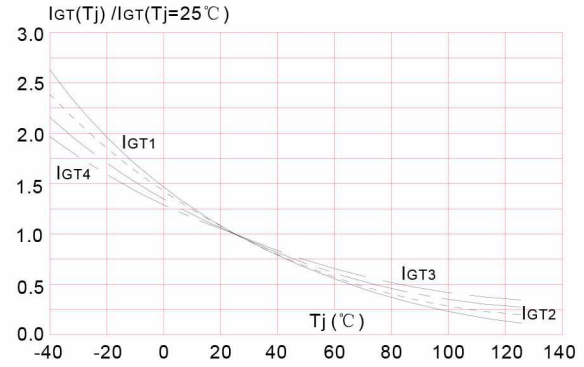
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( I - II -III:  $dI/dt < 50\text{A}/\mu\text{s}$ ; IV:  $dI/dt < 10\text{A}/\mu\text{s}$ )



**FIG.7:** Relative variations of holding current versus junction temperature



**FIG.6:** Relative variations of gate trigger current versus junction temperature



**FIG.8:** Relative variations of latching current versus junction temperature

